

REMARKS

Claims 1 and 34 have been amended. Claims 1, 2, 4, 6, 8, 9 and 34-38 are pending in this application.

The claims have been rejected under 35 U.S.C. 112, first paragraph, as failing to comply with the written description requirement. Applicants traverse the rejection for the following reasons. Specifically, the specification as originally filed provides support for the claimed antennae that includes a discoidal electrode to which ultra high frequency is applied (3), an earth electrode (1) and a dielectric plate (2) provided between the discoidal electrode and the earth electrode, as shown in Fig. 1.

The specification refers to reference numbers 1, 2 and 3 of the figures as the grounded discoidal electrode 1, a discoidal electrode to which ultra high frequency is applied 3, and dielectrics 2. See page 6, lines 27-30 of the specification. It is noted that although reference number 1 is not mentioned in the specification with respect to the description of Fig. 1, one of ordinary skill in the art would realize that the discoidal electrode 1 of Fig. 1 is comparable to the discoidal electrode 1 shown in Fig. 2, which is

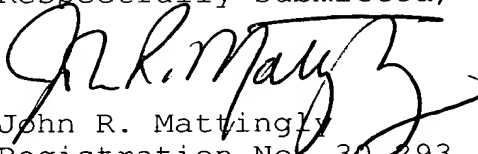
grounded as discussed on page 1, of the specification. Accordingly, the 35 U.S.C. 112, first paragraph rejection should be withdrawn.

Applicants request reconsideration of the rejection of the claims under 35 U.S.C. 103(a) as being unpatentable over Yokogawa et al, EP 0,779,644 A2 (hereinafter Yokogawa). Applicants have amended independent claims 1 and 34 to include the relation between the diameter of the discoidal electrode (3) and the diameter of the wafer to be treated. Specifically, each claim has been amended to set forth that the diameter of the discoidal electrode is not less than that of the wafer. See page 6, lines 27-30 of the specification and the dimensions of the wafer shown in Figs. 9, 13 and 15. That is, the discoidal electrode 3 to which the UHF wave is applied has a diameter of 255 mm and the wafer diameter, taken from Figs. 9, 13 and 15, has a diameter of 200 mm. Note the scale of the wafer with respect to the axis at the 0 position extends from -100 mm to +100 mm. Therefore, the claims as amended are supported by the specification and the relation shown in the drawings, as required.

On the other hand, Yokogawa discloses a discoidal electrode 107 to which the ultra high frequency is applied that is less than that of the diameter of the wafer to be treated, as shown in Fig. 1 of the reference. Accordingly, the reference does not disclose or suggest the invention as claimed in claims 1 and 34. Accordingly, the rejections under 35 U.S.C. 103(a) based on Yokogawa as a primary reference and Nakano et al, U.S. Patent No. 6,155,202 as a secondary reference should be withdrawn.

Entry of the foregoing amendments and allowance of the application is respectfully requested.

Respectfully submitted,

  
John R. Mattingly  
Registration No. 30,293  
Attorney for Applicant(s)

MATTINGLY, STANGER & MALUR  
1800 Diagonal Rd., Suite 370  
Alexandria, Virginia 22314  
(703) 684-1120  
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on January 28 2004, by John R. Mattingly